

MMBV3102LT1G

Silicon Tuning Diode

This device is designed in the Surface Mount package for general frequency control and tuning applications. It provides solid-state reliability in replacement of mechanical tuning methods.

Features

- High Q with Guaranteed Minimum Values at VHF Frequencies
- Controlled and Uniform Tuning Ratio
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

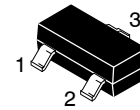
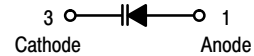
Rating	Symbol	Value	Unit
Reverse Voltage	V _R	30	Vdc
Forward Current	I _F	200	mAdc
Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Junction Temperature	T _J	+125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



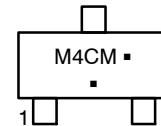
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<http://onsemi.com>



**SOT-23 (TO-236)
CASE 318
STYLE 8**

MARKING DIAGRAM



M4C = Specific Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBV3102LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBV3102LT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$)	$V_{(BR)R}$	30	-	-	Vdc
Reverse Voltage Leakage Current ($V_R = 25 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)	I_R	-	-	0.1	μA
Diode Capacitance Temperature Coefficient ($V_R = 4.0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	TC_C	-	300	-	ppm/ $^\circ\text{C}$

Device	C_T , Diode Capacitance $V_R = 3.0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$ pF			Q , Figure of Merit $V_R = 3.0 \text{ Vdc}$ $f = 50 \text{ MHz}$	C_R , Capacitance Ratio C_3/C_{25} $f = 1.0 \text{ MHz}$	
	Min	Nom	Max	Min	Min	Typ
MMBV3102LT1	20	22	25	200	4.5	4.8

TYPICAL CHARACTERISTICS

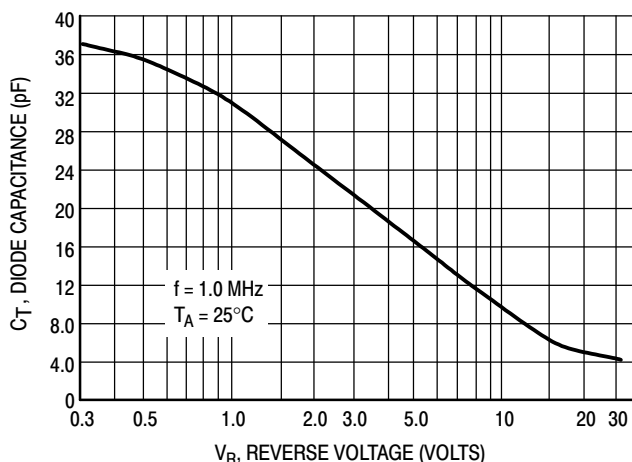


Figure 1. Diode Capacitance

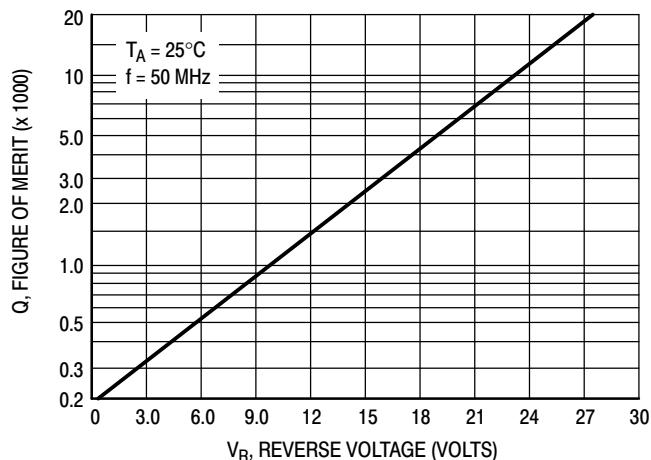


Figure 2. Figure of Merit

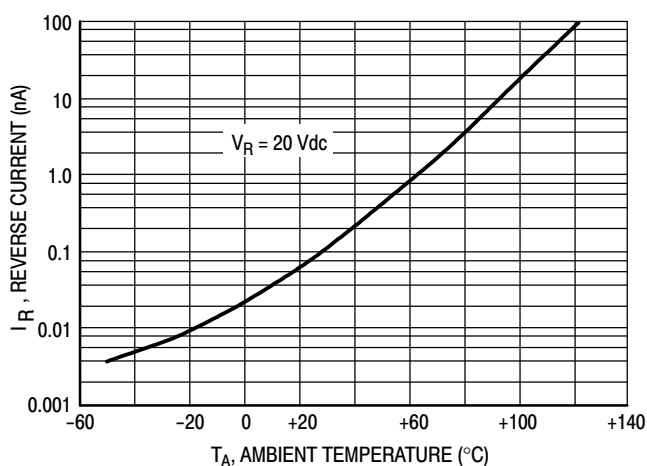


Figure 3. Leakage Current

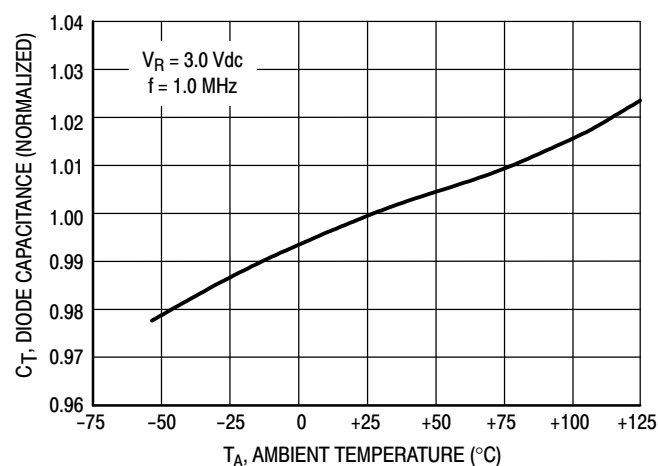


Figure 4. Diode Capacitance

NOTES ON TESTING AND SPECIFICATIONS

1. C_R is the ratio of C_T measured at 3.0 Vdc divided by C_T measured at 25 Vdc.

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